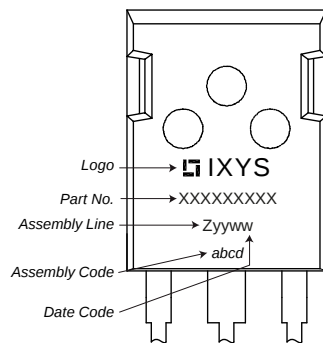


Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			100	μA
		V _R = 600 V	T _{VJ} = 150°C			0.5	mA
V _F	forward voltage drop	I _F = 15 A	T _{VJ} = 25°C			2.53	V
		I _F = 30 A				2.97	V
		I _F = 15 A	T _{VJ} = 150°C			1.58	V
		I _F = 30 A				2.02	V
I _{FAV}	average forward current	T _C = 130°C rectangular d = 0.5	T _{VJ} = 175°C			15	A
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		0.98	V
r _F	slope resistance					27	mΩ
R _{thJC}	thermal resistance junction to case					1.6	K/W
R _{thCH}	thermal resistance case to heatsink				0.25		K/W
P _{tot}	total power dissipation	T _C = 25°C				95	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		110	A
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C		12	pF
I _{RM}	max. reverse recovery current	} I _F = 15 A; V _R = 300 V -di _F /dt = 200 A/μs	T _{VJ} = 25 °C		2		A
t _{rr}	reverse recovery time		T _{VJ} = 100 °C		3		A
			T _{VJ} = 25 °C		25		ns
			T _{VJ} = 100 °C		80		ns
E _{AS}	non-repetitive avalanche energy	I _{AS} = 1 A L = 180 μH		T _{VJ} = 25 °C		0.1	mJ
I _{AR}	repetitive avalanche current	V _A = 1.5·V _R typ. f = 10 kHz				0.1	A

Package TO-247				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal ^{a)}			50	A	
T_{VJ}	virtual junction temperature		-55		175	°C	
T_{op}	operation temperature		-55		150	°C	
T_{stg}	storage temperature		-55		150	°C	
Weight				6		g	
M_D	mounting torque		0.8		1.2	Nm	
F_C	mounting force with clip		20		120	N	

Product Marking



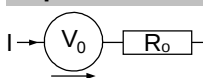
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC30-06B	DSEC30-06B	Tube	30	492647

Similar Part	Package	Voltage class
DSEC30-06A	TO-247AD (3)	600
DSEC29-06AC	ISOPLUS220AB (3)	600

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}\text{C}$



Fast Diode

$V_{0\max}$ threshold voltage

0.98

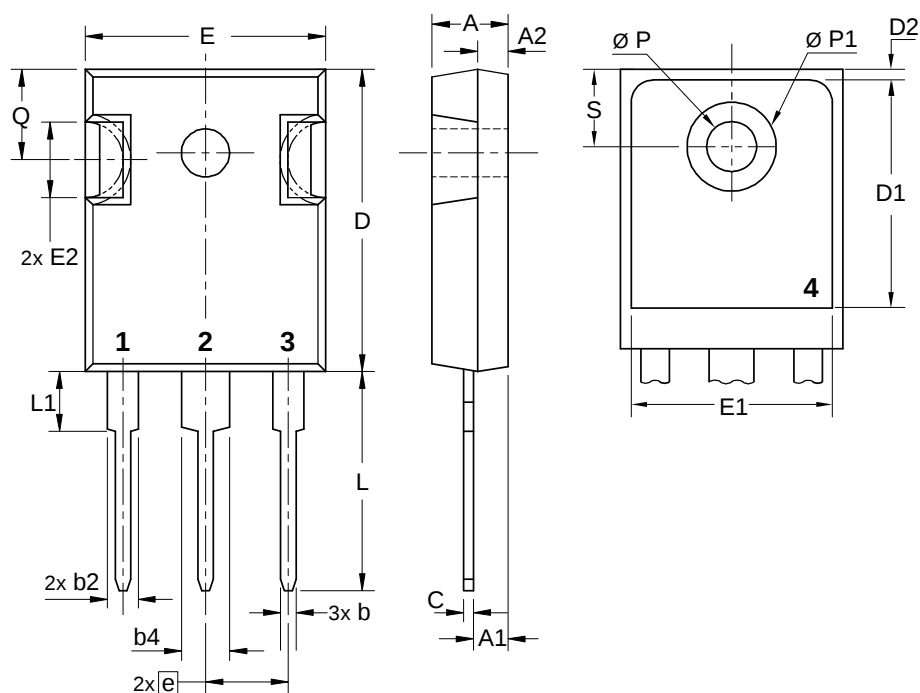
V

$R_{0\max}$ slope resistance *

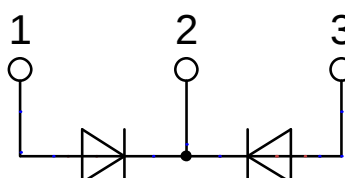
24.5

mΩ

Outlines TO-247



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



Fast Diode

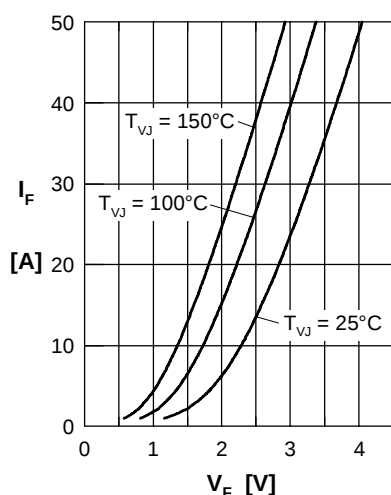


Fig. 1 Forward current I_F versus V_F

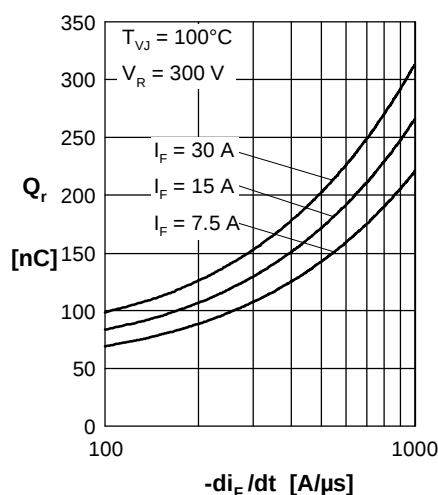


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

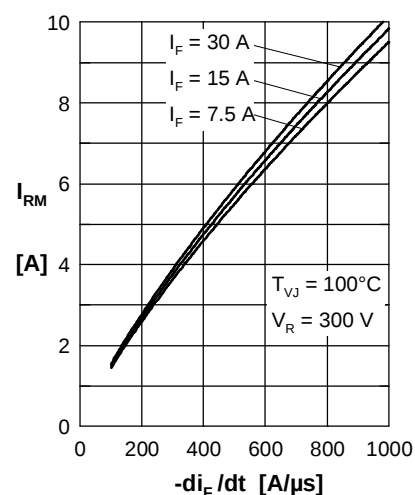


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

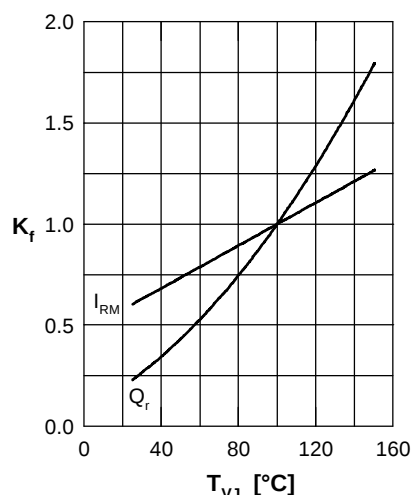


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

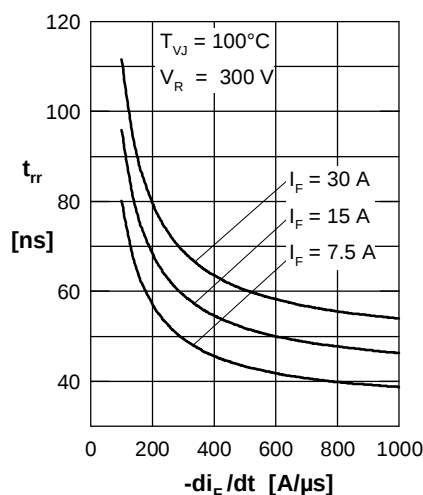


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

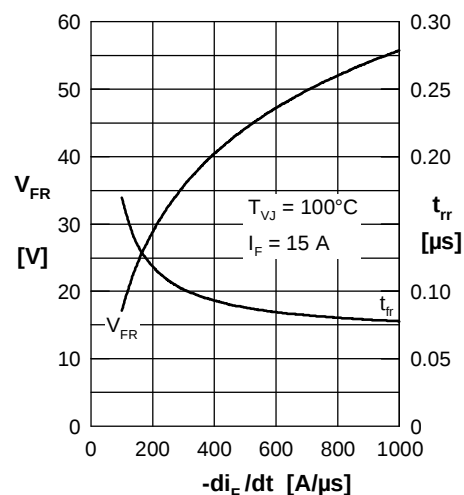


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

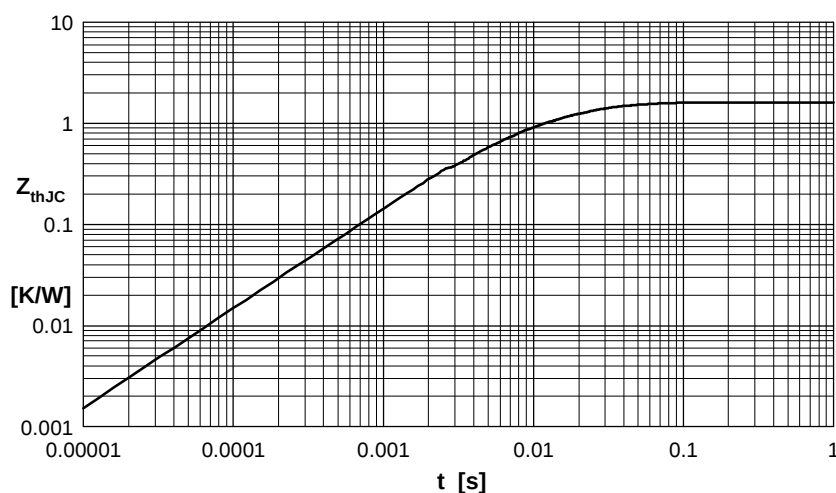


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.908	0.005
2	0.350	0.0003
3	0.342	0.017